

TO-220-2L Plastic-Encapsulate Diode

CSD10H120 Silicon Carbide Schottky Diode

MAIN CHARACTERISTICS

I_o	10A ($T_c \leq 135^\circ\text{C}$)
V_{RRM}	1200V
T_j	175°C
$V_{F(typ)}$	1.5V (@ $T_j=25^\circ\text{C}$) 2.3V (@ $T_j=175^\circ\text{C}$)

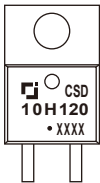
FEATURES

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Temperature-independent performance
- High-speed switching
- Low switching loss
- Low Leakage Current

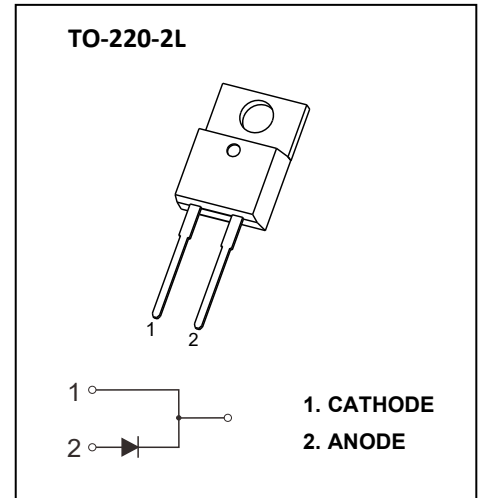
Application

- Industrial Power Supplies
- Power factor correction
- Motor drive traction
- EV charging station
- Solar Inverters

MARKING



CSD10H120 = Device code
 Solid dot = Green molding compound device
 if none, the normal device
 XXXX = Code



MAXIMUM RATINGS ($T_j=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit	
V_{RRM}	Peak repetitive reverse voltage	1200	V	
V_{RWM}	Working peak reverse voltage			
V_R	DC blocking voltage			
$I_{F(AV)}$	Average Forward Current	$T_c \leq 25^\circ\text{C}$	21	A
		$T_c \leq 100^\circ\text{C}$	14	A
		$T_c \leq 135^\circ\text{C}$	10	A
I_{FSM}	Non-Repetitive peak forward surge current (10ms half sine wave)	88	A	
$\int i^2 dt$	$\int i^2 dt$ value ($t_p=10\text{ms}$)	39	A^2s	
P_D	Power dissipation	86	W	
$R_{\theta JC}$	Thermal Resistance From Junction to Case	1.74	$^\circ\text{C}/\text{W}$	
T_j	Junction temperature	-55~175	$^\circ\text{C}$	
T_{stg}	Storage temperature	-55~175	$^\circ\text{C}$	

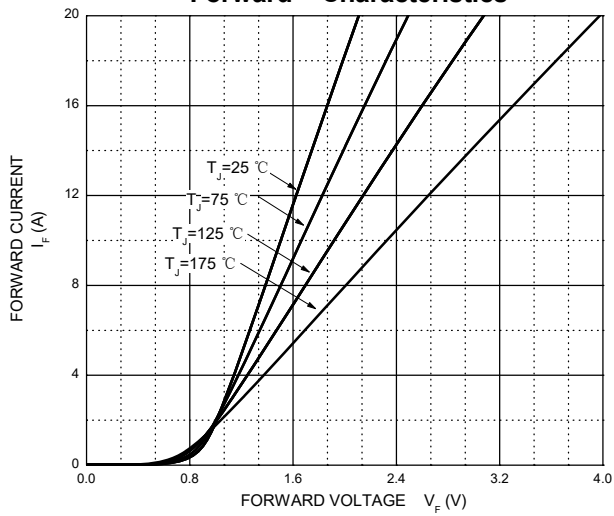
Typical Characteristics

ELECTRICAL CHARACTERISTICS($T_j=25^{\circ}\text{C}$ unless otherwise specified)

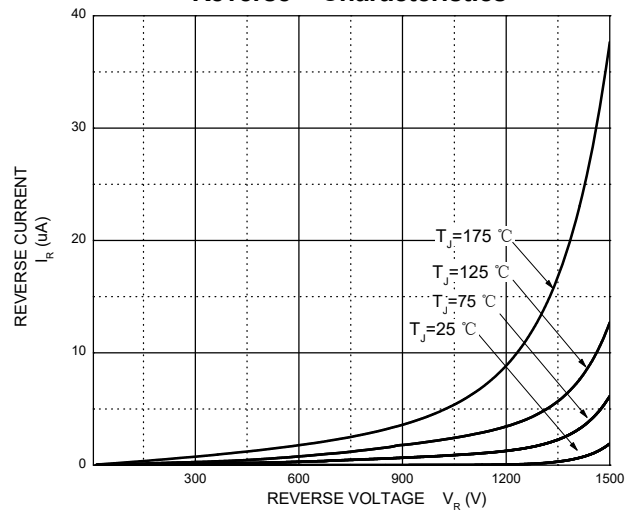
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	1200			V
Reverse current	I_R	$V_R=1200\text{V}$	$T_j=25^{\circ}\text{C}$	5	50	μA
			$T_j=175^{\circ}\text{C}$	20	200	μA
Forward voltage	V_F	$I_F=10\text{A}$	$T_j=25^{\circ}\text{C}$	1.5	1.8	V
			$T_j=175^{\circ}\text{C}$	2.3	3.0	V
Total capacitance	C	$V_R=0\text{V}, f=1\text{MHz}$		672		pF
		$V_R=400\text{V}, f=1\text{MHz}$		43		pF
		$V_R=800\text{V}, f=1\text{MHz}$		35		pF
Total capacitive charge	Q_C	$V_R=800\text{V}$ $Q_C=\int_0^{V_R} C(V)dV$		50		nC
Capacitance Stored Energy	E_C	$V_R=800\text{V}$ $E_C=\int_0^{V_R} C(V) \cdot VdV$		15		μJ

Typical Characteristics

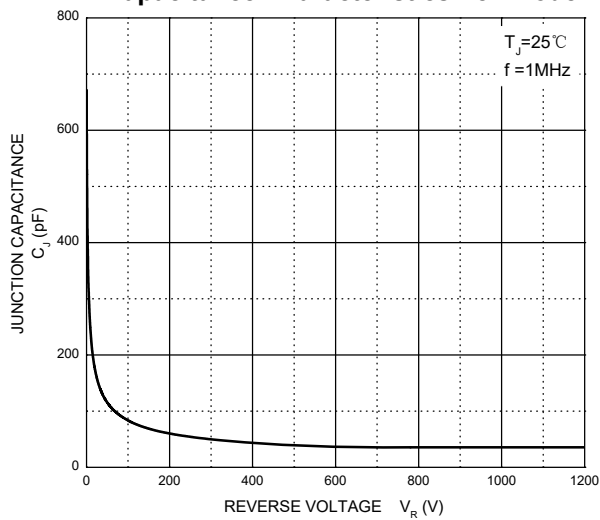
Forward Characteristics



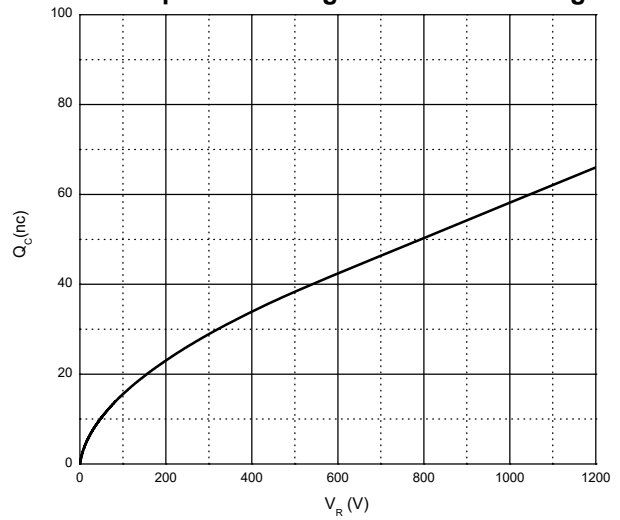
Reverse Characteristics



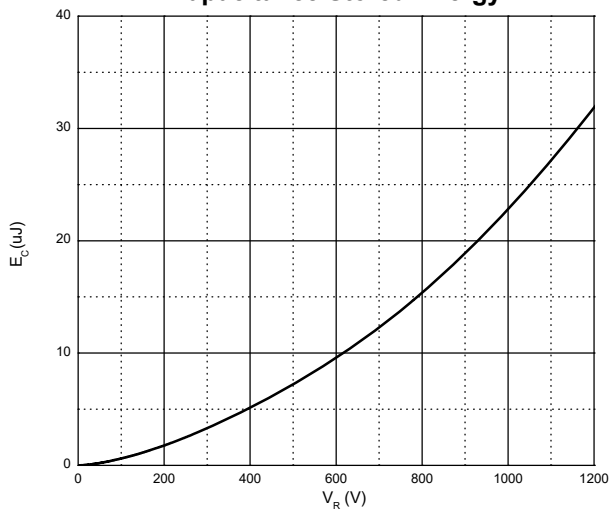
Capacitance Characteristics Per Diode



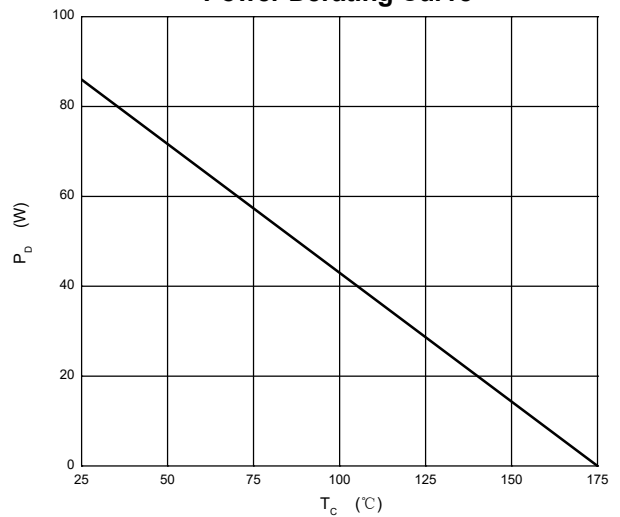
Total Capacitive Charge vs. Reverse Voltage



Capacitance Stored Energy

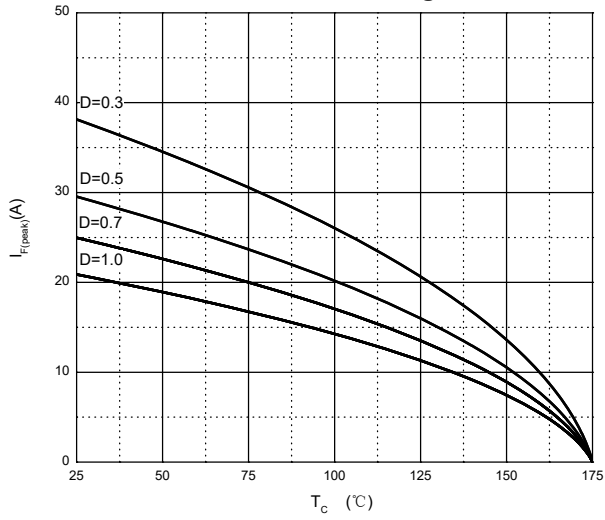


Power Derating Curve

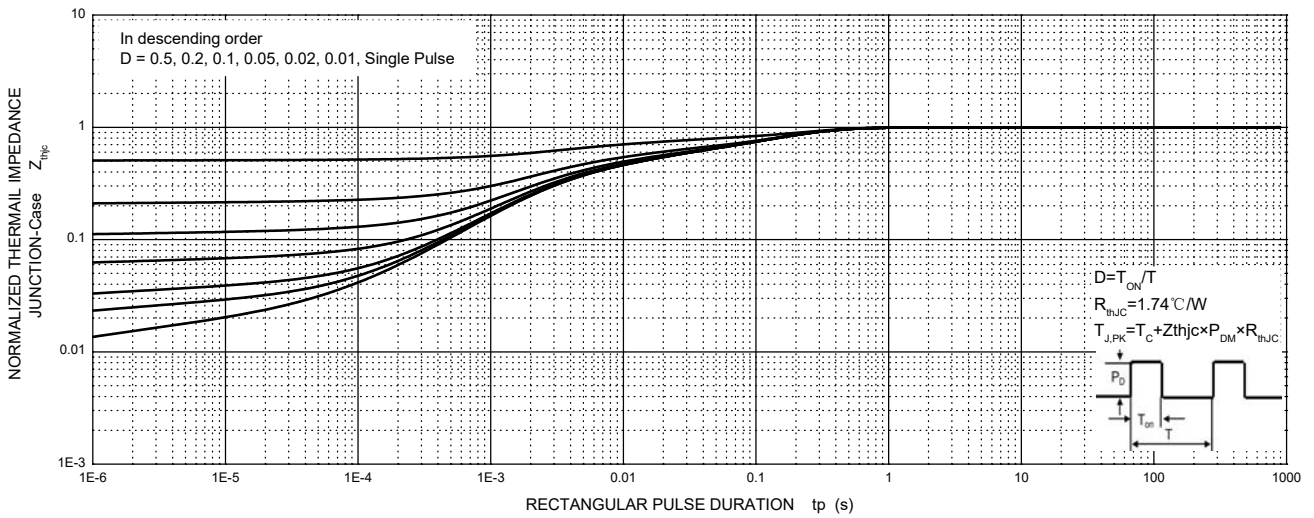


Typical Characteristics

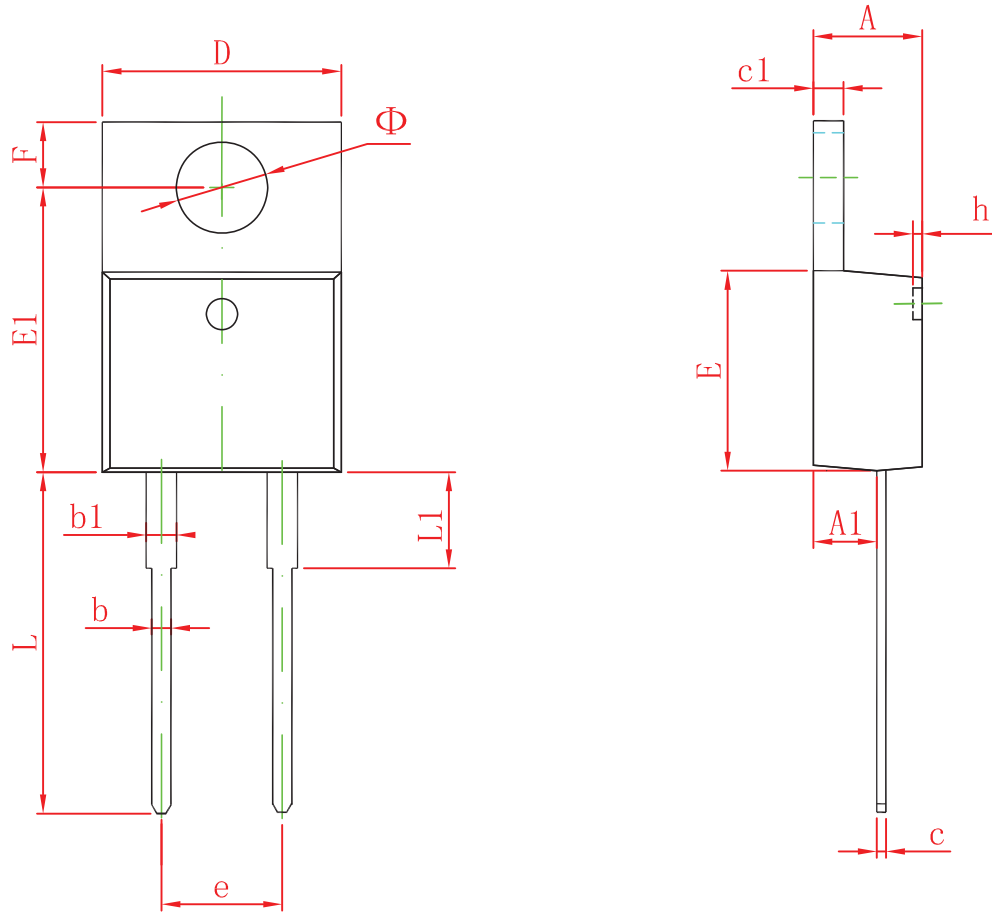
Current Derating



CSD10H120 Transient Thermal Impedance, Junction-Case



TO-220-2L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.450	4.750	0.175	0.187
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.300	0.500	0.012	0.020
c1	1.170	1.370	0.046	0.054
D	9.830	10.330	0.387	0.407
E	8.500	8.900	0.335	0.350
E1	12.050	12.650	0.474	0.498
e	5.080 TYP		0.200 TYP	
F	2.540	2.940	0.100	0.116
h	0.100 TYP		0.004 TYP	
L	13.300	13.800	0.523	0.543
L1	3.540	3.940	0.139	0.155
Φ	3.735	3.935	0.147	0.155